N on-Ferm i liquid behavior of the electrical resistivity at the ferrom agnetic quantum critical point

D.Bodea[y], M.Crisan, I.Grosu, and I.Tifrea[z]

Department of Theoretical Physics, University of Cluj, 3400 ClujN apoca, Romania

W e propose a model for the non-Ferm ibehavior in the proximity of the quantum phase transition induced by the strong polarization of the electrons due to local magnetic moments. The self-consistent R enormalization G roup methods have been used to calculate the tem perature dependence of the electrical resistivity and speci c heat. The T⁵⁻³ dependence of resistivity and the T ln T dependence of the speci c heat show that the magnetic in purities drive a ferrom agnetic quantum phase transition and near the critical point the system present a non-Ferm i liquid behavior. The model is in good agreement with the experimental data obtained for N i_x Pd_{1 x} alloy.

I. IN TRODUCTION

Deviations from the standard Fermi liquid description in heavy fermion systems (HFS) have been associated to the proximity of the quantum phase transition (QPT). De ned as phase transitions at T = 0, QPT's are usually driven by quantum uctuations controlled by a non-thermal parameter, namely by in purities, pressure or magnetic elds.[1] Most of these low temperature magnetic QPT's are from paramagnetic to antiferrom agnetic state, but recently HFS undergoing a param agnetic to ferrom agnetic phase transitions were identied. Example of HFS which are close to ferrom agnetic order are Th₁ xUxCu₂Si₂,[2] MnSi,[3] and NixPd₁ x.[4] The itinerant-electron ferrom agnetic state in these materials is induced by pressure (MnSi) or impurities (Th₁ xUxCu₂Si₂ and NixPd₁ x).

Th₁ $_{x}U_{x}Cu_{2}Si_{2}$ for concentrations x 0.15 presents ferrom agnetic order. Experim ental data in these com – pounds show a non-Ferm iliquid behavior for C=T / ln T and a critical temperature, T_c, as low as 12K for the x = 0.15 sample.[2] However, the magnetic susceptibility data present a eld dependance even at temperatures bellow T_c, a behavior characteristic for weak itinerant ferrom agnets.

In the case of MnSiexperim ental results show ed the existence of a rst-order phase transition induced by pressure, the critical tem perature decreasing towards absolute zero at a pressure value p_c ' 14:6 kbar. For $p > p_c$ a non-Ferm i liquid behavior of the resistivity as function oftem perature is reported, T.[3] The phenom enological theory [3] based on the interaction of the electrons with the overdam ped spin uctuations at low energies, can explain the occurrence of the non-Ferm istate. The quantum transport anom alies of the itinerant-electron ferrom agnetic state have been discussed also by Belitz, Kirkpatrik, Narayanan and Vojta (BKNV) [5], the non-Ferm i behavior of the system being proved based on the scaling approach. The model from Ref. [5] predicts a rst order phase transition and it is in an excellent agreem ent with the QPT driven by pressure in MnSi [3].

N $i_x P d_{1-x}$ at a N i concentration $x_c = 0.025$ presents ferrom agnetic order assumed to occur in the itinerant electron system of P d atom s due to a strong polarization

of these electrons by magnetic in purities (in this case N i). The transition critical temperature depends on the N i concentration as $(x \ x_c)^{3=4}$ in the critical region. In the same region of the phase diagram, experimental data reveal a T ⁵⁼³ dependance of the relative resistivity, , and a T ln T dependance of the speci cheat, C (T).[4] A ll these experimental data clearly identify the non-Ferm i character of the electronic excitations close to the quantum critical point (Q C P). These results were successfully described in terms of phenom enological spin- uctuation m odels.[6]

In this work we extend the D oniah-W ohlfarth m odel,[7] proposed for the explanation of the itinerant electron ferrom agnetic state driven by in purities in N i_x P d_{1 x} compounds, to the critical region and we calculate using renorm alization group m ethods the tem perature dependence of the resistivity and the speci c heat. We will apply the Hertz-M illis [8, 9] version of the Renorm alization G roup m ethod (RNG) to the D oniah-W ohlfarth m odel taking into consideration the quantum e ects at nite tem perature and extract the e ects of the spin uctuations on the system . The self-consistent renorm alization group theory, given by M oriya [10] will be used to calculate the tem perature dependence of the electrical resistivity.

II. M ODEL

W e consider that the uctuations in the magnetization in the critical region are given by the action:

$$S_{eff} = S_{eff}^{(2)} + S_{eff}^{(4)}$$
; (1)

where

$$S_{eff}^{(2)} = \frac{1}{2} X_{q}^{1} (q) j (q) j^{2} (2)$$

and

$$S_{eff}^{(4)} = \frac{u}{4} \frac{X}{q_1} \frac{X}{q_4} (q_1) \dots (q_4) (q_4 + q_4) + q_4$$
(3)

Here we introduce the notation $q = (q;!_n), !_n$ being the bosonic M atsubara frequencies, and

$$X = k_{\rm B} T \frac{X}{n} \frac{Z}{(2)^{\rm d}} :$$

In Eqs. (2)-(3) (q) is the uctuation propagator and u is the coupling constant.

In the follow ing we consider that the spin in purity has a very strong polarization e ect on the electrons and at a critical concentration $x = x_c$ a new phase, which is in fact a ferrom agnetic phase, can be reached. This model has been proposed rst by Donniach and Wolhfarth [7] using a single in purity approximation. The susceptibility of the polarized electrons was given (see Ref. [7]) as

$$(q;!) = \frac{0 (q;!)}{1 \qquad I + 2 \frac{J^2 R^0}{J R!} \qquad 0 (q;!)}; \qquad (4)$$

where $_0$ (q;!) is the susceptibility of the electronic system. In Eq. (4) J is the exchange interaction between electrons and localized spins and I is the interaction between electrons. The parameters R and R⁰ have been calculated as

$$R = \frac{1}{N} \frac{X}{k} (n_{k\#} - n_{k"})$$
(5)

and

$$R^{0} = x hS^{z}i; \qquad (6)$$

 ${\bf x}$ being the impurity concentration of the magnetic moments with spin S .

The dynamic susceptibility $_0$ (q;!) has the form [10]

$$\int_{0}^{1} (q;!) ' \int_{0}^{1} (0;0) 1 \quad D q^{2} + iC \frac{!}{q} ; (7)$$

where D and C are constants. We approximate (q;!) from Eq. (4) as

$$(q;!) = \frac{1}{{_0}^1 (q;!) I \frac{2^{IR^0}}{R}}; \qquad (8)$$

a results which based on Eq. (4) can be written as

$$(q;!) = \frac{1}{_{0}(x) + aq^{2} + \frac{1}{q}};$$
 (9)

where a and are constants, and $_0(x)$ is given by

$$_{0}(\mathbf{x}) = _{0}^{1} \quad \mathbf{I} \quad \frac{\mathbf{JR}^{0}}{\mathbf{R}} :$$
 (10)

The parameter $_0(x)$, with a linear dependance on the impurity concentration, measures the distance from the QCP.

The model is valid only for systems in which the bcalm om ents give a strongly polarization of the itinerant electrons and this is typically for m etals as Pd which is param agnetic and the Stoner criterium cannot be satis ed only due to the electron-electron interaction. For this particular system we do not expect localization effects, excepting the case of nonm agnetic in purities, but this cannot drive the system in the ordered phase.

This model, described by Eqs. (1), (2) and (9), can be treated using the Renorm alization G roup method, in the version proposed by Hertz [8] and M illis [9]. Following Refs. [8, 9] we perform the standard scaling k ! $k^0=b$, !_n ! ! !_n⁰= b^z , z being the dynam ic critical exponent. We obtain the following ow equations:[11]

$$\frac{dT(l)}{dl} = zT(l); \qquad (11)$$

$$\frac{d(1)}{d1} = (3 z) (1);$$
(12)

$$\frac{d}{dl} = 2 (l) + 2(n + 2)f_1u(l);$$
(13)

$$\frac{du(l)}{dl} = [4 \quad (d+z)]u(l) \quad (n+8) \notin u^2(l); \quad (14)$$

where d is the spatial dimension, f_i are functions characteristic for the model (see Ref. [9]) and l = ln b is the scaling variable. Additionally, the system free energy will scale as:

$$\frac{dF(l)}{dl} = (d + z)F(l) + f_3;$$
(15)

 f_3 being again a characteristic function of the model.

III. SPECIFIC HEAT AND RESISTIVITY

The evaluation of the renorm alized free energy F [T (1)] based on Eq. (15) will lead to the temperature dependence of the speci c heat which by de nition can be calculated as the second derivative of the free energy with respect to the temperature, C (T) = T ($\ell^2 F = \ell T^2$). In general there will be two distinct contributions to the renorm alized free energy, associated to a quantum domain, T (1) 1, and to a classical one, T (1) 1. For m ore details on the calculation of the free energy see R efs. [9, 11]. However, as the form of the system susceptibility m atch the corresponding form for a ferrom agnetic system, if we consider the d = 3 case, the speci c heat is obtained as

$$C(T) = {}_{0}T + {}_{1}T \ln T;$$
 (16)

 $_0$ and $_1$ being constants, a result which clearly show that the behavior of the considered system is non-Ferm i, as corrections to the linear temperature dependance of the speci c heat are logarithm ic. This result is in agreement with the experimental data presented in Ref. [4]. W e have to m ention that a similar behavior was obtained using RG m ethod for a system in the proximity of the Lifshitz quantum critical point.[12] R ecent experimental data in silicon MOSFETs[13] suggested a QPT to a ferrom agnetically ordered state in d = 2. An analysis of the speci c heat behavior for the d = 2 case was done in R ef. [11] suggesting a di erent tem perature dependance of the speci c heat. In order to calculate the tem perature dependence of the resistivity we apply the self-consistent theory of uctuations to the action given by Eq. (1). This can be done in the version of 1=n expansion (n being the number of components of the bosonic eld) applied to the 4 action. Using the approximation j 4 j 2 < j² j > j² j the renormalized parameter (x) can be calculated from the following self-consistent equation:

$$(\mathbf{x}) = {}_{0}(\mathbf{x}) + \frac{\mathbf{u}}{2} \frac{\mathbf{n}}{2} + 1 \quad \mathbf{k}_{\mathrm{B}} \mathrm{T} \stackrel{\mathrm{X}}{\underset{!_{n}}{\overset{\mathrm{Z}}{\overset{\mathrm{Z}}{(2)^{3}}}} \frac{\mathrm{d}^{3}\mathbf{k}}{(2)^{3}} \frac{1}{(\mathbf{x}) + \mathbf{k}^{2} + \frac{j!_{n}j}{\mathbf{k}}} :$$
(17)

The sum mation over the bosonic M atsubare frequencies on the second term in the right hand side (rhs) of Eq. (17) can be performed analytically leading to the following expression:

$$(\mathbf{x}) = {}_{0}(\mathbf{x}) + \frac{\mathbf{u}}{2} \frac{\mathbf{n}}{2} + 1 \qquad \frac{\mathbf{z}}{(2)^{3}} \frac{\mathbf{d}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{z}}{\mathbf{u}^{3}} \frac{\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{k}}{\mathbf{u}^{3}\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}}{\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}} \frac{\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}\mathbf{u}^{3}}{\mathbf{u}^{3}\mathbf{u}^$$

The tem perature dependence of the QPT parameter (x) can be extracted if we consider Eq. (18) at the QCP in order to elim in the bare QPT parameter $_{0}(x)$. A coordingly, we obtain

$$\begin{aligned} (x) &= \frac{u}{2} \frac{n}{2} + 1 \qquad \frac{d^3k}{(2)^3} \int_{0}^{2-k} \frac{d!}{m} \quad \text{oth} \quad \frac{!}{2k_B T} \qquad 1 \quad \frac{\frac{!}{k}}{(-k_B)^2 + \frac{!}{k}^2} \\ &+ \frac{u}{2} \frac{n}{2} + 1 \qquad \frac{Z}{(2)^3} \int_{0}^{2-k} \frac{d!}{m} \quad \frac{\frac{!}{k}}{(-k_B)^2 + \frac{!}{k}^2} \quad \frac{\frac{!}{k}}{(-k_B)^2 + \frac{!}{k}^2} \quad \frac{\frac{!}{k}}{(-k_B)^2 + \frac{!}{k}^2} : \end{aligned}$$
(19)

For T = 0 we will show that T holds. In this approximation the rst integral in the rhs of Eq. (19) becomes:

$$I_{1} = 2k_{B}T \frac{2}{(2)^{3}} \frac{d^{3}k}{0} \frac{d^{2}k_{B}T}{\frac{d!}{2}} \frac{d!}{\frac{k}{2}} \frac{\frac{1}{k}}{A^{2} + \frac{1}{k}^{2}}; \quad (20)$$

where $A = (x) + k^2$. Performing the integral over ! we get:

$$I_{1} = \frac{k_{B} T}{6^{3}} \frac{k_{B} T}{0} \frac{dy \frac{\arctan y}{y^{4=3}}}{(y^{4=3})^{4=3}}$$

= C_{1} (k_{B} T)^{4=3}; (21)

where $y = k_B T = k^3$; y_c , associated with the upper critical wave-vector k_c , has been substituted by in nity. C_1 is a constant. The second integral from the rhs of Eq. (19), I_2 , is:

$$I_{2} = \int_{0}^{Z} \frac{k}{2} \frac{d!}{\frac{1}{k}} \frac{\frac{1}{k}}{\frac{1}{k^{2} + \frac{1}{k}}^{2}} \frac{\frac{1}{k}}{\frac{1}{k^{4} + \frac{1}{k}}^{2}} ; \quad (22)$$

and can be performed if one introduce a new variable $y = k = {}^{1=2} w$ it an upper cut-o $y_c = k_c [(x)] {}^{1=2}$. The nal result can be express as:

$$I_2 = C_2 (x) :$$
 (23)

Based on Eqs. (19), (21) and (23) we obtain for (x) the following temperature dependance:

$$(x;T) = C (u;n) (k_B T)^{4=3};$$
 (24)

which is nite for n ! 1. This result can be inverted in order to extract the concentration dependence of the critical temperature. If one consider that the temperature can be approximated by the critical value (T_c), and that in the rst order (x) $_0$ (x) we have

$$T_{c}(x) (x x)^{3=4};$$
 (25)

a result which is in agreem ent with the one discussed in Ref. [4].

The temperature dependance of the resistivity can be extracted as the imaginary part of the self-energy, obtained as a result of electrons interacting with the ferromagnetic uctuations. In the one-loop approximation we have:

$$(k;i!_{n}) = g^{2}k_{B}T \int_{q;i!_{1}}^{X} G(k+q;i!_{n}+i!_{1}) D(q;i!_{1});$$

(26)

where g^2 is the coupling constant, G (k;i!_n) is the electronic G reen function,

$$G(k; i!_n) = \frac{1}{i!_n} (k);$$
 (27)

with $!_n = (2n + 1)k_B T$, and D $(q;i!_1)$ has the same form with (q;!) given by Eq. (9) whit $_0(x)$ replaced by (x). Perform ing the sum mation over $!_1$ in Eq. (26) we obtain:

$$(k; i!_{n}) = \begin{array}{c} 2 & X & Z & q \\ q & \frac{dz}{A^{2} + \frac{z}{q}} \\ q & q & A^{2} + \frac{z}{q} \end{array}$$

$$[n_{B}(z) + n_{F}(z + !)] \quad [! + z & (k + q)]; \quad (28)$$

where n_B (z) is the Bose function and n_F (z) is the Ferm i function. For jzj T we approximate n_B (z) + n_F (z) T=z and performing the analytical continuation i! n ! ! + i we calculate

Im ^R (k_F;0) '

$$g^{2} \frac{X Z q}{q} \frac{dz}{A^{2} + \frac{z}{q}^{2}} [z (k+q)]$$
 (29)

which leads to the following expression for the imaginary part of the self-energy

Im ^R (k_F;0) = const
$$\frac{(k_B T)^3}{(T)}$$
: (30)

U sing now Eq. (24) we obtain the temperature dependence of the scattering time $1 = _{eff} = _{m}$ Im ^R as:

$$\frac{1}{\text{eff}} = \text{const} (k_{\text{B}} \text{T})^{5=3}; \qquad (31)$$

which gives for the temperature dependent resistivity (T) = (T) (0) the following behavior

$$(T)$$
 $(k_B T)^{5=3}$; (32)

in agreem ent with the experim ental data from Ref. [4].

IV. CONCLUSION

In conclusion, we presented a model for the ferrom agnetic QPT driven by the magnetic in purities which polarize the Ferm i liquid close to the Stoner instability. The

- [y] Present Address: Universite Bordeaux 1, C P M O H ., 33405 Talence, C edex France
- [z] P resent address: D epartm ent of P hysics and A stronom y, The U niversity of Iowa, Iowa C ity, IA 52242, U SA.
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result can be regarded as a generalization of the D oniach and W ohlfarth [7]mean-eldmodel for the case of QPT.As a general result we conclude that the system presents a non-Ferm ibehavior in the critical region around a QCP. The non-Ferm i character of the system is sustained by a T ln T behavior of the speci c heat correction term , and by an electrical resistivity which presents a T⁵⁼³ dependence. Both these results are in good agreem ent with the experim ental data reported in Ref. [4]. A sim ilar tem perature dependance of the resistivity was obtained by Mathon [14] using a simple molecular eld theory. However, despite a good agreem ent between the calculated and experim ental values of the resistivity, M athon calculations are not able to explain the non-Ferm ibehavior of the speci c heat and do not take into account the quantum e ects observed in N $i_x P d_1_x$, making the model inadequate for the proper description of the QPT in this particular system. A phenom enological description of the QPT was also made by Lonzarich.[6] W e also explain the concentration dependance of the critical tem perature, our result being in good agreem ent with the experim ental data.

We mention that this model is dierent from the BKNV [5] model, in which the spin susceptibility for the d = 3 case is considered as $(q; ! = 0) = _0 + q^2 \ln (p_F = q)$. This form of (q) has been carefully analyzed by Millis [15] and at the present time new experimental data are needed for a con mation of this spin susceptibility. Recently, Belitz and Kirkpatrick [16] have been reconsidered the QPT in the clean itinerant-electron ferrom agnet. The coupling of the order parameter uctuations to the soft ferm ionic uctuations lead to a theory which is very di erent than theories based on the Hertz-M illis m odel. The main point in the new version of the BKNV theory is that the uctuations can change the rst order phase transition in a second order one. How ever, the occurrence of two dynamical exponents z and z for the two kind of uctuations makes the two theories very di erent, even if in any case the mean eld behavior can explain the experim ental data.

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